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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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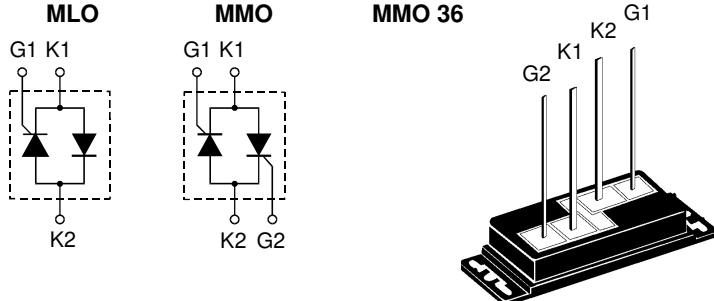
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## AC Controller Modules

**I<sub>RMS</sub> = 39 A**  
**V<sub>RRM</sub> = 1200-1600 V**

V <sub>RSM</sub> V <sub>DSM</sub>	V <sub>RRM</sub> V <sub>DRM</sub>	Type
1200	1200	MLO 36-12io1
1600	1600	MMO 36-16io1



Symbol	Test Conditions	Maximum Ratings		
I <sub>RMS</sub>	T <sub>K</sub> = 85°C, 50 - 400 Hz (for single controller)	39	A	
I <sub>TRMS</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	28	A	
I <sub>TAVM</sub>	T <sub>K</sub> = 85°C; (180° sine)	18	A	
I <sub>TSM</sub>	T <sub>VJ</sub> = 45°C; V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	360 390	A A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	320 350	A A
I <sup>2</sup> t	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	645 630	A <sup>2</sup> s A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	510 510	A <sup>2</sup> s A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> f = 50 Hz, t <sub>p</sub> = 200 μs V <sub>D</sub> = 2/3 V <sub>DRM</sub> I <sub>G</sub> = 0.3 A di <sub>G</sub> /dt = 0.3 A/μs	repetitive, I <sub>T</sub> = 150 A  non repetitive, I <sub>T</sub> = I <sub>TAVM</sub>	100 500	A/μs A/μs
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; R <sub>GIK</sub> = ∞; method 1 (linear voltage rise)	V <sub>DR</sub> = 2/3 V <sub>DRM</sub>	1000	V/μs
P <sub>GM</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> I <sub>T</sub> = I <sub>TAVM</sub>	t <sub>p</sub> = 30 μs t <sub>p</sub> = 300 μs	10 5	W W
P <sub>GAVM</sub>			0.5	W
V <sub>RGM</sub>			10	V
T <sub>VJ</sub>			-40...+125	°C
T <sub>VJM</sub>			125	°C
T <sub>stg</sub>			-40...+125	°C
V <sub>ISOL</sub>	50/60 Hz, RMS I <sub>ISOL</sub> ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~ V~
M <sub>d</sub>	Mounting torque	(M3) (UNF 4-32)	0.7 ± 0.1 6 ± 0.9	Nm lb.in.
Weight	typ.		15	g

Data according to IEC 60747 and to a single thyristor/diode unless otherwise stated.  
 IXYS reserves the right to change limits, test conditions and dimensions.

Symbol	Test Conditions	Characteristic Values		
$I_R, I_D$	$T_{VJ} = T_{VJM}$ ; $V_R = V_{RRM}$ ; $V_D = V_{DRM}$	≤	5	mA
$V_T$	$I_T = 45 \text{ A}$ ; $T_{VJ} = 25^\circ\text{C}$	≤	1.49	V
$V_{TO}$	For power-loss calculations only	0.85	V	
$r_T$		15	mΩ	
$V_{GT}$	$V_D = 6 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	1.0	V
$I_{GT}$	$V_D = 6 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	≤	65	mA
		≤	120	mA
$I_{GM}$	$t_p = 50 \mu\text{s}$ , $f = 60 \text{ Hz}$ , $I_T = I_{TAVM}$		6	A
$V_{GD}$	$T_{VJ} = T_{VJM}$ ;	≤	0.2	V
$I_{GD}$	$V_D = 2/3 V_{DRM}$	≤	1	mA
$I_L$	$T_{VJ} = 25^\circ\text{C}$ ; $t_p = 10 \mu\text{s}$ , $V_D = 6 \text{ V}$ $I_G = 0.3 \text{ A}$ ; $dI_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	150	mA
$I_H$	$T_{VJ} = 25^\circ\text{C}$ ; $V_D = 6 \text{ V}$ ; $R_{GK} = \infty$	≤	100	mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}$ ; $V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}$ ; $dI_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤	2	μs
$t_q$	$T_{VJ} = T_{VJM}$ ; $I_T = 11 \text{ A}$ , $t_p = 200 \mu\text{s}$ ; $-dI/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$ ; $dv/dt = 10 \text{ V}/\mu\text{s}$ ; $V_D = 2/3 V_{DRM}$	typ.	150	μs
$R_{thJC}$	per thyristor/diode; DC current	1.3	K/W	
	per module	0.65	K/W	
$R_{thJK}$	per thyristor/diode; DC current	1.5	K/W	
	per module	0.75	K/W	
$d_s$	Creeping distance on surface	6	mm	
$d_A$	Creepage distance in air	6	mm	
$a$	Max. allowable acceleration	50	$\text{m/s}^2$	

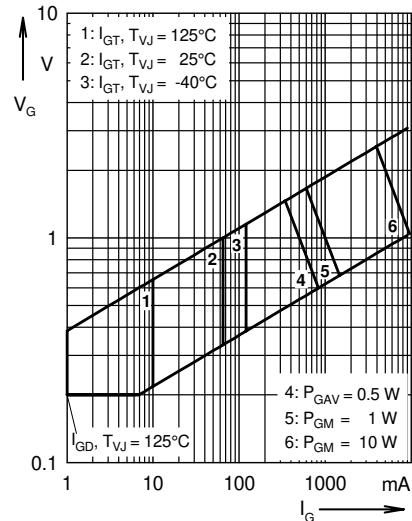


Fig. 1 Gate trigger characteristics

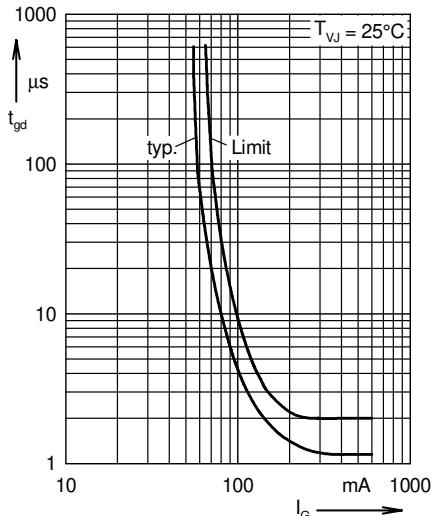


Fig. 2 Gate trigger delay time

Dimensions in mm (1 mm = 0.0394")  
MLO 36

MMO 36

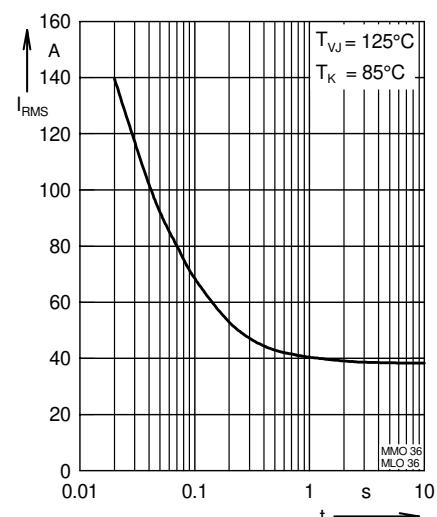
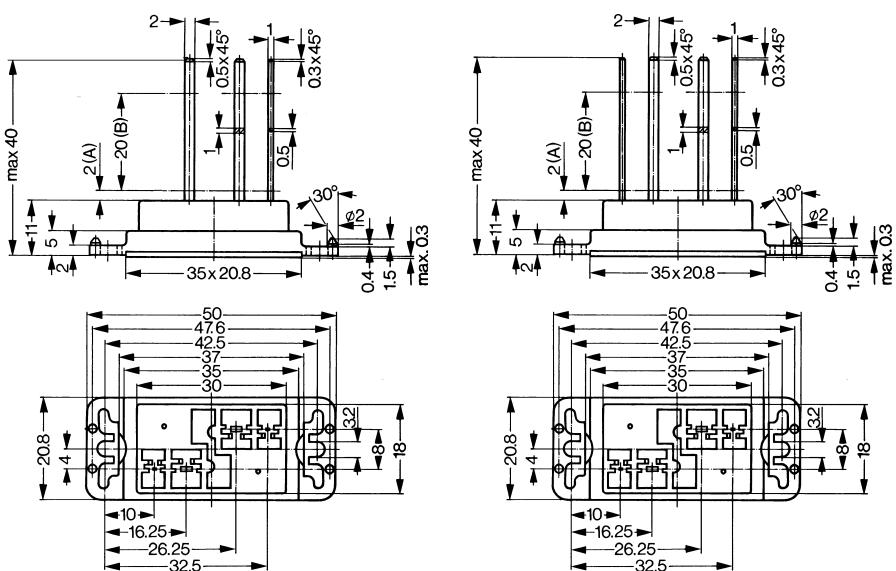


Fig. 3 Rated RMS current versus time (360° conduction)

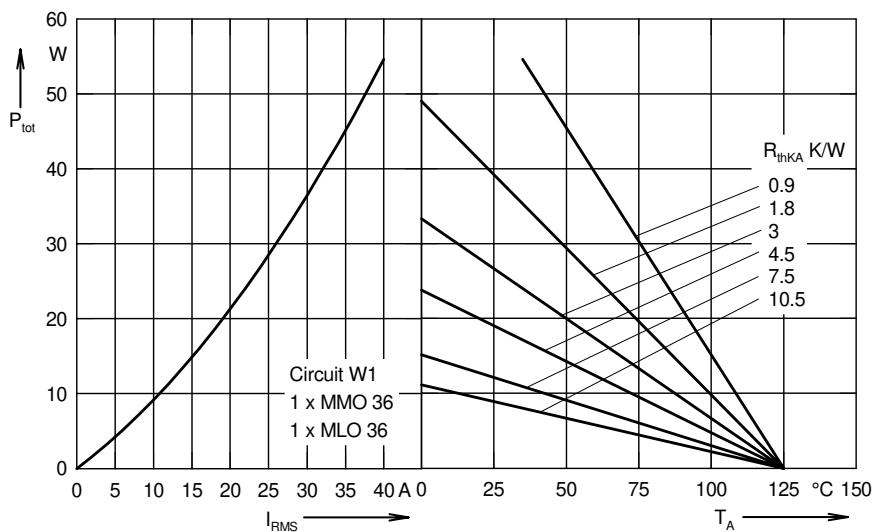


Fig. 4 Load current capability for single phase AC controller

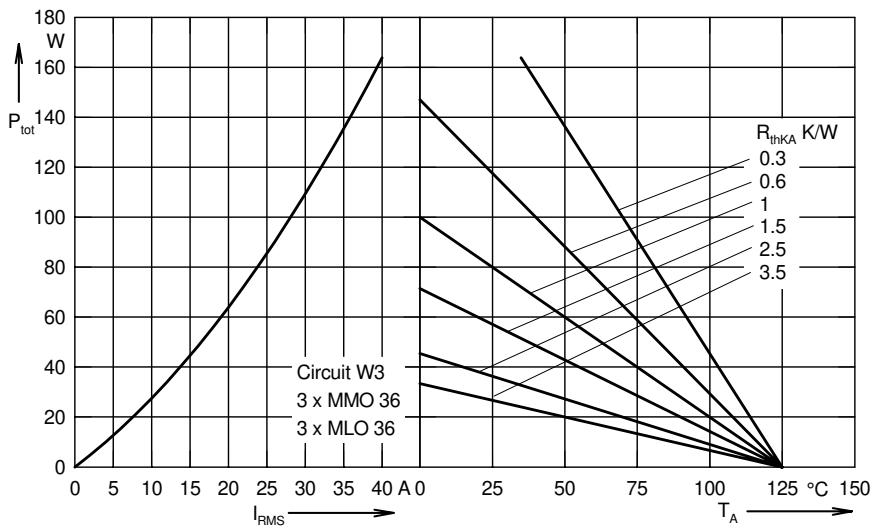


Fig. 6 Load current capability for three phase AC controller: 3xMMO 36/MLO 36

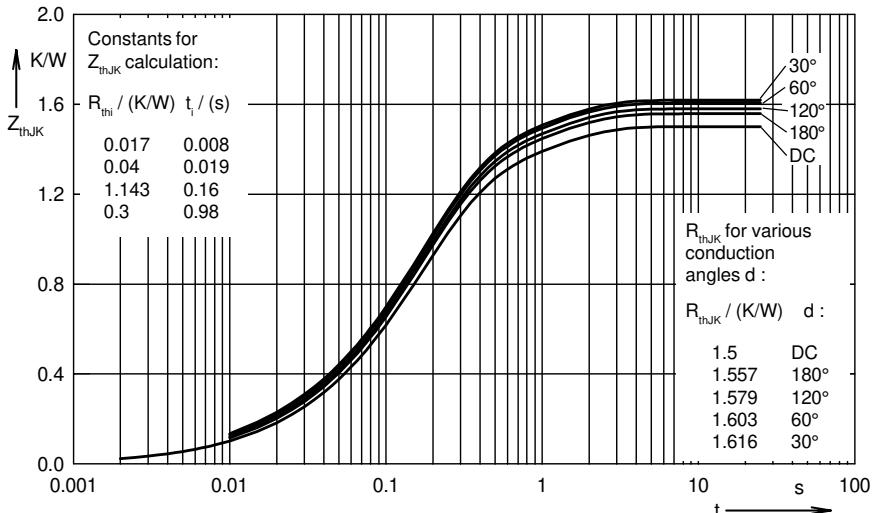


Fig. 8 Transient thermal impedance junction to heatsink (per thyristor or diode)

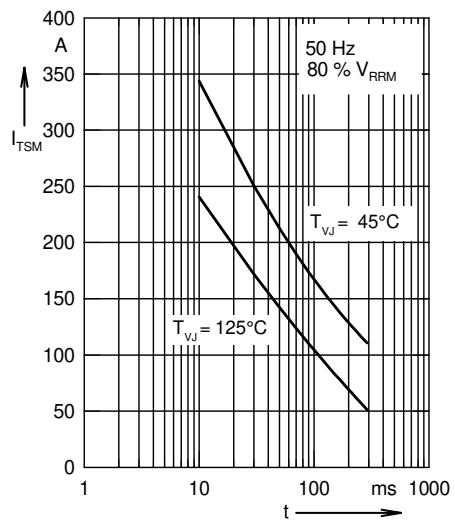


Fig. 5 Surge overload current  
 $I_{TSM}$ ,  $I_{FSM}$ : Crest value,  $t$ : duration

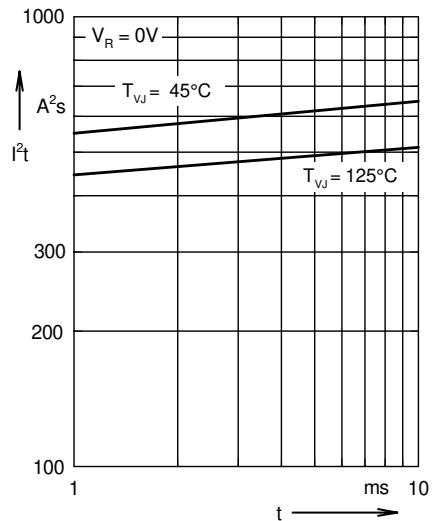


Fig. 7  $I^2t$  versus time (1-10 ms)

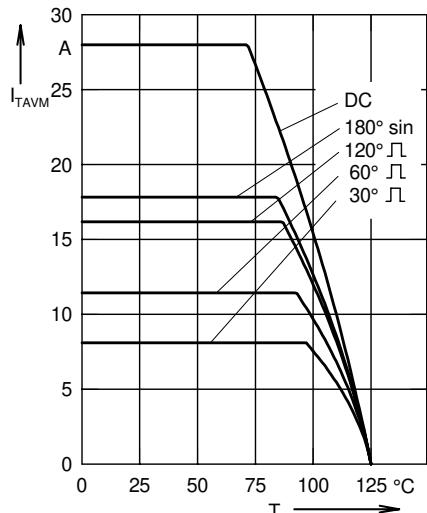


Fig. 9 Maximum on-state current versus heatsink temperature